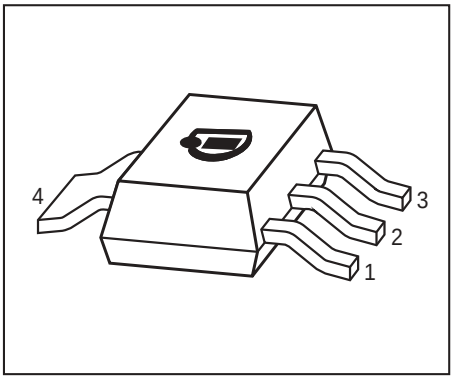
NPN Silicon RF Transistor*



- For low-distortion broadband output amplifier stages in antenna and telecommunication systems up to 2 GHz at collector currents from 120 mA to 250 mA
- Power amplifiers for DECT and PCN systems
- Integrated emitter ballast resistor
- f_T = 5.5 GHz
- Pb-free (RoHS compliant) package[1)]
- Qualified according AEC Q101

* Short term description

ESD (**E**lectro**s**tatic **d**ischarge) sensitive device, observe handling precaution!

Type	Marking	Pin Configuration						Package
BFG235	BFG235	1 = E	2 = B	3 = E	4 = C	-	-	SOT223

Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-emitter voltage	V_{CEO}	15	V
Collector-emitter voltage	V_{CES}	25	
Collector-base voltage	V_{CBO}	25	
Emitter-base voltage	V_{EBO}	2	
Collector current	I_C	300	mA
Base current	I_B	40	
Total power dissipation[2)] $T_S \leq 80°C$	P_{tot}	2	W
Junction temperature	T_j	150	°C
Ambient temperature	T_A	-65 ... 150	
Storage temperature	T_{stg}	-65 ... 150	

[1]Pb-containing package may be available upon special request
[2]T_S is measured on the collector lead at the soldering point to the pcb

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Thermal Resistance

Parameter	Symbol	Value	Unit
Junction - soldering point[1)]	R_{thJS}	≤ 35	K/W

Electrical Characteristics at T_A = 25°C, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics					
Collector-emitter breakdown voltage I_C = 1 mA, I_B = 0	$V_{(BR)CEO}$	15	-	-	V
Collector-emitter cutoff current V_{CE} = 25 V, V_{BE} = 0	I_{CES}	-	-	200	µA
Collector-base cutoff current V_{CB} = 10 V, I_E = 0	I_{CBO}	-	-	100	nA
Emitter-base cutoff current V_{EB} = 1 V, I_C = 0	I_{EBO}	-	-	2	µA
DC current gain- I_C = 200 mA, V_{CE} = 8 V, pulse measured	h_{FE}	75	120	160	-

[1]For calculation of R_{thJA} please refer to Application Note Thermal Resistance

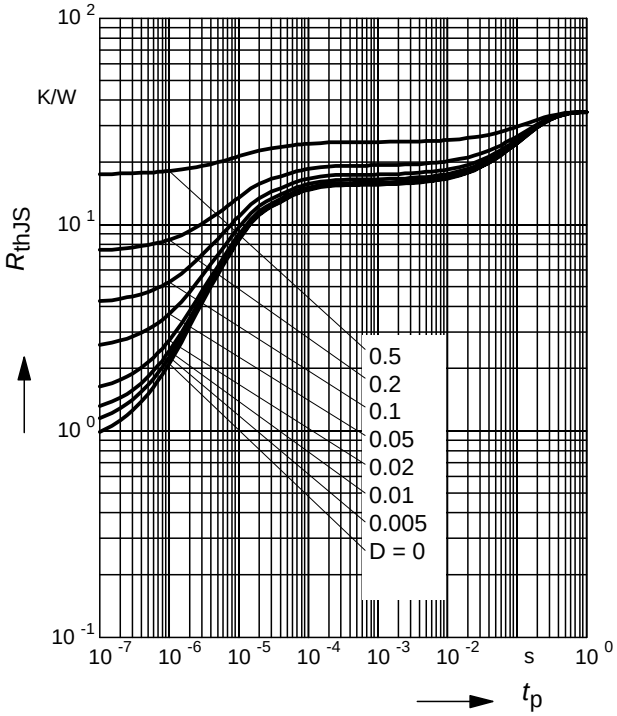
Electrical Characteristics at T_A = 25°C, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
AC Characteristics (verified by random sampling)					
Transition frequency I_C = 200 mA, V_{CE} = 8 V, f = 200 MHz	f_T	4	5.5	-	GHz
Collector-base capacitance V_{CB} = 10 V, f = 1 MHz, V_{BE} = 0 , emitter grounded	C_{cb}	-	2.2	3	pF
Collector emitter capacitance V_{CE} = 10 V, f = 1 MHz, V_{BE} = 0 , base grounded	C_{ce}	-	1.5	-	
Emitter-base capacitance V_{EB} = 0.5 V, f = 1 MHz, V_{CB} = 0 , collector grounded	C_{eb}	-	14	-	
Noise figure I_C = 60 mA, V_{CE} = 8 V, Z_S = Z_{Sopt}, f = 900 MHz	F	-	1.7	-	dB
Power gain, maximum available[1)] I_C = 200 mA, V_{CE} = 8 V, Z_S = Z_{Sopt}, Z_L = Z_{Lopt}, f = 900 MHz	G_{ma}	-	12.5	-	
Transducer gain I_C = 200 mA, V_{CE} = 8 V, Z_S = Z_L = 50Ω, f = 900 MHz	$\lvert S_{21e}\rvert^2$	-	6.5	-	dB
Third order intercept point at output V_{CE} = 8 V, I_C = 200 mA, f = 900 MHz, Z_S = Z_L = 50Ω	IP_3	-	33	-	dBm

[1] $G_{ma} = |S_{21}/S_{12}| (k-(k^2-1)^{1/2})$

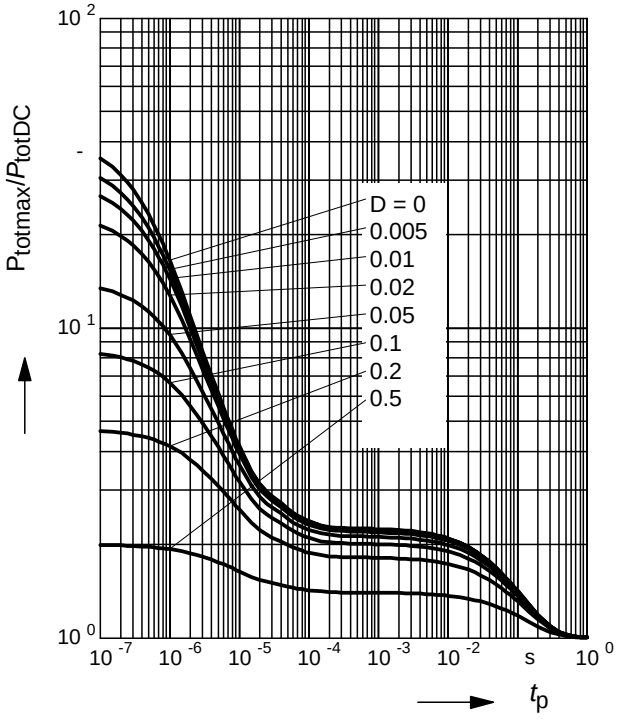
Total power dissipation $P_{tot} = f(T_S)$

Permissible Pulse Load $R_{thJS} = f(t_p)$

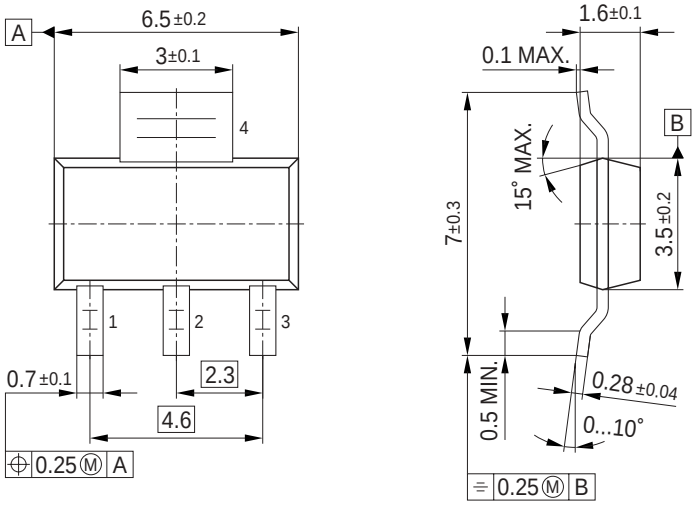


Permissible Pulse Load

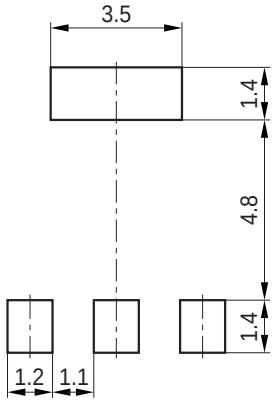
$P_{totmax}/P_{totDC} = f(t_p)$



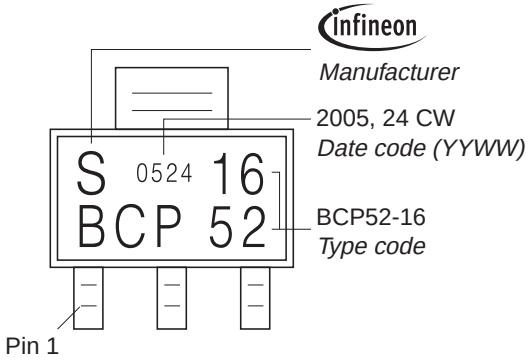
Package Outline



Foot Print

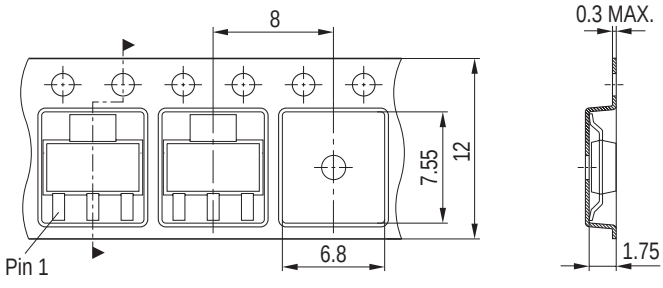


Marking Layout (Example)



Packing

Reel ø180 mm = 1.000 Pieces/Reel
Reel ø330 mm = 4.000 Pieces/Reel



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